

L Number	Hits	Search Text	DB	Time stamp
-	78	117/9.ccls. and amorphous same (silicon or germanium or si or ge or sige)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:19
-	52	117/9.ccls. and amorphous same (silicon or germanium or si or ge or sige) same (heat adj treat\$4 or rapid adj thermal or rta or rtp or ptp or anneal\$4 or laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:28
-	8	117/9.ccls. and amorphous same (germanium or ge or sige) same (heat adj treat\$4 or rapid adj thermal or rta or rtp or ptp or anneal\$4 or laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:43
-	24	117/4-9.ccls. and amorphous same (germanium or ge or sige) same (heat adj treat\$4 or rapid adj thermal or rta or rtp or ptp or anneal\$4 or laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 15:56
-	42	(117/4-9.ccls. and amorphous near4 (silicon or si) same (heat adj treat\$4 or rapid adj thermal or rta or rtp or ptp or anneal\$4 or laser)) and (ge or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:08
-	24	(117/4-9.ccls. and amorphous near4 (silicon or si) same (laser)) and (ge or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 16:48
-	1	((amorphous near3 (silicon or si) and amorphous near3 (germanium or ge or sige)) same (anneal\$4 or laser) and TFT) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 17:56
-	9	(ge or germanium or sige or silicon adj germanium) same second near3 amorphous near2 layer and TFT	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 11:23
-	43	crystal\$4 same second near3 amorphous near2 layer and TFT	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 11:55
-	2	crystal\$4 same second near3 amorphous near2 layer and TFT and first near3 (ge or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 13:16
-	3	TFT and first near3 (ge or germanium) same crystal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 13:18
-	7	TFT and first near3 (ge or germanium) same amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 13:25
-	25	electrode same insulat\$4 same amorphous same germanium and TFT	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 15:15

-	16	TFT same anneal\$4 same laser same (xenon or mercury or metal adj halide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 15:20
-	40	anneal\$4 same laser same (mercury or metal adj halide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 15:25
-	39	crystal\$4 near3 improv\$3 same amorphous near5 (silicon or germanium or si or ge or sige) same TFT	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 09:40
-	1	crystal\$4 near3 improv\$3 same amorphous near5 (germanium or ge or sige) and TFT	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 15:49
-	24	crystal\$4 near3 improv\$3 same (germanium or ge or sige) and TFT	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:15
-	110	amorphous near3 (silicon or si) same plasma adj (CVD or chemical adj vapor adj deposit\$4) and turbo adj molecular adj pump\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:23
-	10	amorphous near3 (silicon or si) same plasma adj (CVD or chemical adj vapor adj deposit\$4) same turbo adj molecular adj pump\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:35
-	7	amorphous same silicon same two adj step same crystal\$4 same laser and tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:49
-	10	amorphous same two adj step same crystal\$4 same laser and tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 09:40
-	79	second near5 anneal\$4 same laser and crystal\$4 near5 laser and tft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 17:45